imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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MG0675S-BN4MM

Littelfuse

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Features

Applications

High frequency

- High short circuit capability, self limiting short circuit current
- V_{CE(sat)} with positive temperature coefficient
- Fast switching and short tail current

switching application

• Medical applications

• Free wheeling diodes with fast and soft reverse recovery

RoHS 7

Low switching losses

Motion/servo control

UPS systems

Agency Approvals

AGENCY	AGENCY FILE NUMBER
91	E71639

Module Characteristics (T_c = 25°C, unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Тур	Max	Unit
T _J max	Max. Junction Temperature				175	°C
T _{J op}	Operating Temperature		-40		150	°C
T _{stg}	Storage Temperature		-40		125	°C
V _{isol}	Insulation Test Voltage	AC, t=1min		3000		V
CTI	Comparative Tracking Index		350			
Torque	Module-to-Sink	Recommended (M6)	3		5	N∙m
Torque	Module Electrodes	Recommended (M5)	2.5		5	N∙m
Weight				160		g

Absolute Maximum Ratings (T_c = 25°C, unless otherwise specified) Symbol Values Unit Parameters **Test Conditions** IGBT V_{CES} T_=25°C 600 V Collector - Emitter Voltage V_{GES} Gate - Emitter Voltage ±20 V T_c=25°C 100 А DC Collector Current I_{c} T_c=70°C 75 А Repetitive Peak Collector Current t_=1ms 150 А I_{CM} $\mathsf{P}_{\mathrm{tot}}$ Power Dissipation Per IGBT 250 W Diode V Repetitive Reverse Voltage T_=25°C 600 V T_c=25°C 100 А $\mathsf{I}_{\mathrm{F(AV)}}$ Average Forward Current T_c=70°C 75 А Repetitive Peak Forward Current t_=1ms 150 А I_{FRM} l²t $T_{1} = 125^{\circ}C$, t=10ms, $V_{B} = 0V$ 660 A²s

Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

Electrical and Thermal Specifications (T_c = 25°C, unless otherwise specified)

Symbol	Parameters	Test Conditions		Min	Тур	Max	Unit
IGBT							
V _{GE(th)}	Gate - Emitter Threshold Voltage	$V_{ce} = V_{ce}$, $I_c = 1.2 \text{mA}$		4.9	5.8	6.5	V
	Collector - Emitter	$I_c=75A, V_{GE}=15V, T_J=25^{\circ}C$ $I_c=75A, V_{GE}=15V, T_J=125^{\circ}C$		1	1.45	1.9	V
$V_{\text{CE(sat)}}$	Saturation Voltage				1.6		V
1	Collector Leakage Current	$\frac{V_{CE}=600V, V_{GE}=0V, T_{J}=25^{\circ}C}{V_{CE}=600V, V_{GE}=0V, T_{J}=125^{\circ}C}$				1	mA
I _{CES}						5	mA
I _{GES}	Gate Leakage Current	V _{CE} =0V,V _{GE} =±	15V, T _J =125°C	-400		400	nA
R_{Gint}	Integrated Gate Resistor				0		Ω
Q _{ge}	Gate Charge	V_{cc} =300V, I _c =75A , V _{GE} =±15V			0.8		μC
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f =1MHz			4.6		nF
C _{res}	Reverse Transfer Capacitance				0.145		nF
+	Turn - on Delay Time		T _J =25°C		25		ns
t _{d(on)}	Ium - on Delay Inne		T _J =125°C		25		ns
t,	Rise Time	V _{cc} =300V	T _J =25°C		20		ns
r			T _J =125°C		20		ns
t _{d(off)}	Turn - off Delay Time	I _c =75A	T _J =25°C		210		ns
d(off)		R ₆ =5.1Ω	T _J =125°C		240		ns
t,	FallTime		T _J =25°C		60		ns
T		V _{GE} =±15V	T _J =125°C		70		ns
Eon	Turn - on Energy	Inductive Load	T _J =25°C	ļ	0.35		mJ
011			T_=125°C		0.5		mJ
E _{off}	Turn - off Energy		T_=25°C		2.4		mJ
			T_ =125°C		2.8		mJ
I _{sc}	Short Circuit Current	$t_{_{psc}}{\leq}6\mu S$, $V_{_{GE}}{=}15V; T_{_{J}}{=}125^{\circ}C, V_{_{CC}}{=}360V$			380		А
R _{thJCD}	Junction-to-Case Thermal Resi	stance (Per IGBT)			1	0.6	K/W
Diode							
V _F	Forward Voltage	I _F =75A , V _{GE} =			1.55	1.95	V
۴F		I _F =75A , V _{GE} =0V, T _J =125°C			1.50		V
I _{rrm}	Max. Reverse Recovery Current	I _F =75A , V _R =300V di _F /dt=-4000A/μs T _J =125°C			115		A
Q _{rr}	Reverse Recovery Charge				6.0		μC
E _{rec}	Reverse Recovery Energy				1.5		mJ
R_{thJC}	Junction-to-Case Thermal Resis	stance (Per Diode)				0.9	K/W

Figure 1: Typical Output Characteristics

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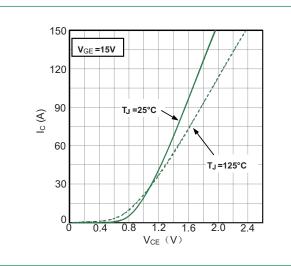


Figure 3: Typical Transfer characteristics

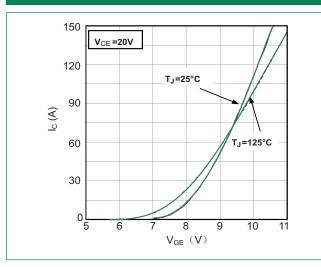


Figure 5: Switching Energy vs. Collector Current

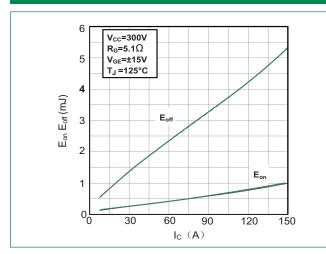


Figure 2: Typical Output characteristics

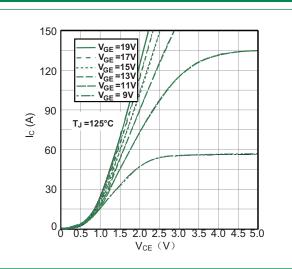


Figure 4: Switching Energy vs. Gate Resistor

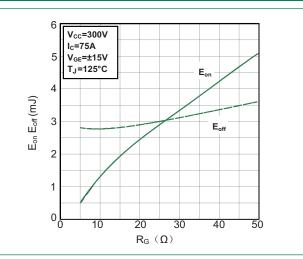


Figure 6: Reverse Biased Safe Operating Area

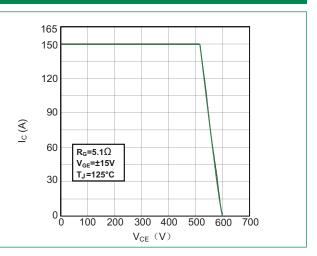


Figure 7: Diode Forward Characteristics

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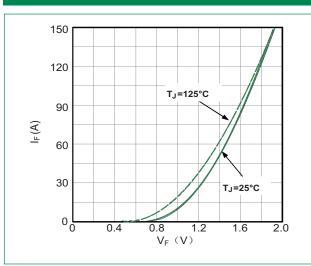


Figure 9: Switching Energy vs. Forward Current

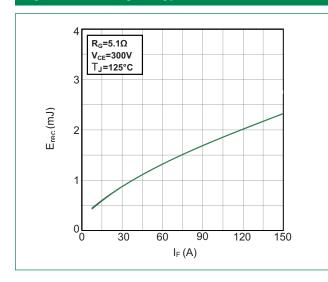


Figure 8: Switching Energy vs. Gate Resistor

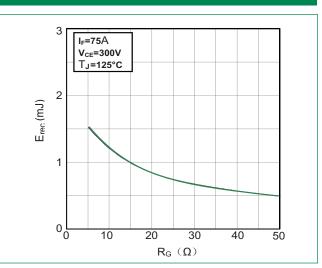
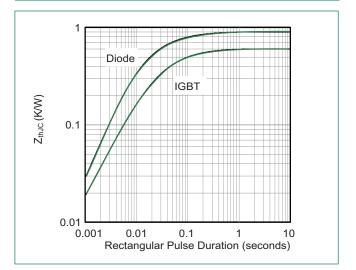
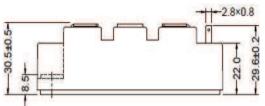
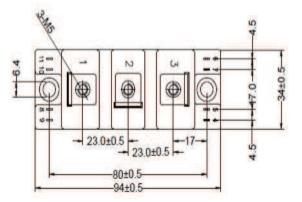


Figure 10: Transient Thermal Impedance



Dimensions-Package S

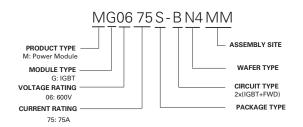




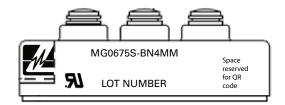
Packing Options

Part Number	Marking	Weight	Packing Mode	M.O.Q
MG0675S-BN4MM	MG0675S-BN4MM	160g	Bulk Pack	100

Part Numbering System



Part Marking System



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Circuit Diagram

